

Product specification Supersedes data of 1996 Feb 26 IC23 Data Handbook

1998 Jan 16



74ABT126

FEATURES

- Quad bus interface
- 3-State buffers
- Live insertion/extraction permitted
- Output capability: +64mA/-32mA
- Latch-up protection exceeds 500mA per JEDEC Std 17
- ESD protection exceeds 2000V per MIL STD 883 Method 3015 and 200V per Machine Model
- Power-up 3-State
- Inputs are disabled during 3-State mode

QUICK REFERENCE DATA

DESCRIPTION

The 74ABT126 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT126 device is a quad buffer that is ideal for driving bus lines. The device features four Output Enables (OE0, OE1, OE2, OE3), each controlling one of the 3-State outputs.

SYMBOL	PARAMETER	CONDITIONS T _{amb} = 25°C; GND = 0V	TYPICAL	UNIT
t _{PLH} t _{PHL}	Propagation delay An to Yn	$C_L = 50 pF; V_{CC} = 5V$	2.9	ns
C _{IN}	Input capacitance	$V_{I} = 0V \text{ or } V_{CC}$	4	pF
C _{OUT}	Output capacitance	Outputs disabled; V _O = 0V or V _{CC}	7	pF
Iccz	Total supply current	Outputs disabled; $V_{CC} = 5.5V$	65	μΑ

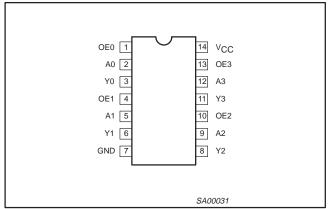
ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
14-Pin Plastic DIP	-40°C to +85°C	74ABT126 N	74ABT126 N	SOT27-1
14-Pin plastic SO	-40°C to +85°C	74ABT126 D	74ABT126 D	SOT108-1
14-Pin Plastic SSOP Type II	-40°C to +85°C	74ABT126 DB	74ABT126 DB	SOT337-1
14-Pin Plastic TSSOP Type I	-40°C to +85°C	74ABT126 PW	74ABT126PW DH	SOT402-1

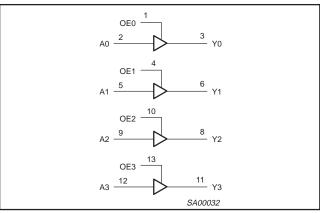
PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
2, 5, 9, 12	A0 – A3	Data inputs
3, 6, 8, 11	Y0 – Y3	Data outputs
1, 4, 10, 13	OE0 – OE3	Output enable inputs
7	GND	Ground (0V)
14	V _{CC}	Positive supply voltage

PIN CONFIGURATION

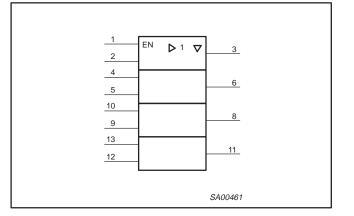


LOGIC SYMBOL



74ABT126

LOGIC SYMBOL (IEEE/IEC)



FUNCTION TABLE

INP	INPUTS					
OEn	An	Yn				
н	L	L				
н	Н	н				
L	Х	Z				

H = High voltage level

L = Low voltage level

X = Don't care Z = High impedance "off" state

ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
I _{IK}	DC input diode current	V ₁ < 0	-18	mA
VI	DC input voltage ³		-1.2 to +7.0	V
I _{OK}	DC output diode current	V _O < 0	-50	mA
V _{OUT}	DC output voltage ³	output in Off or High state	-0.5 to +5.5	V
I _{OUT}	DC output current	output in Low state	128	mA
T _{stg}	Storage temperature range		-65 to 150	°C

NOTES:

 Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction

temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C. 3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIM	UNIT	
STWBOL	FARAIVIETER	Min	Max	UNIT
V _{CC}	DC supply voltage	4.5	5.5	V
VI	Input voltage	0	V _{CC}	V
V _{IH}	High-level input voltage	2.0		V
V _{IL}	Low-level Input voltage		0.8	V
I _{ОН}	High-level output current		-32	mA
I _{OL}	Low-level output current		64	mA
Δt/Δv	Input transition rise or fall rate	0	10	ns/V
T _{amb}	Operating free-air temperature range	-40	+85	°C

Product specification

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DC ELECTRICAL CHARACTERISTICS

					LIMITS			
SYMBOL	PARAMETER	TEST CONDITIONS	T _{amb} = +25°C			T _{amb} = to +	–40°C 85°C	
			Min Typ Max		Min	Max	1	
V _{IK}	Input clamp voltage	$V_{CC} = 4.5V; I_{IK} = -18mA$		-0.9	-1.2		-1.2	V
		V_{CC} = 4.5V; I_{OH} = –3mA; V_{I} = V_{IL} or V_{IH}	2.5	2.9		2.5		V
V _{OH}	High-level output voltage	V_{CC} = 5.0V; I_{OH} = –3mA; V_{I} = V_{IL} or V_{IH}	3.0	3.4		3.0		V
		V_{CC} = 4.5V; I_{OH} = –32mA; V_{I} = V_{IL} or V_{IH}	2.0	2.4		2.0		V
V _{OL}	Low-level output voltage	V_{CC} = 4.5V; I_{OL} = 64mA; V_{I} = V_{IL} or V_{IH}		0.35	0.55		0.55	V
I _I	Input leakage current	V_{CC} = 5.5V; V_I = GND or 5.5V		±0.01	±1.0		±1.0	μΑ
I _{OFF}	Power-off leakage current	V_{CC} = 0.0V; V_{O} or $V_{I} \le 4.5V$		±5.0	±100		±100	μA
I _{PU} /I _{PD}	Power-up/down 3-State output current ³	V_{CC} = 2.1V; V_O = 0.5V; V_I GND or V_{CC} ; V_{OE} = Don't care		±5.0	±50		±50	μA
I _{OZH}	3-State output High current	V_{CC} = 5.5V; V_{O} = 2.7V; V_{I} = V_{IL} or V_{IH}		1.0	50		50	μΑ
I _{OZL}	3-State output Low current	V_{CC} = 5.5V; V_{O} = 0.5V; V_{I} = V_{IL} or V_{IH}		-1.0	-50		-50	μΑ
I _{CEX}	Output High leakage current	V_{CC} = 5.5V; V_{O} = 5.5V; V_{I} = GND or V_{CC}		5.0	50		50	μΑ
Ι _Ο	Output current ¹	$V_{CC} = 5.5V; V_{O} = 2.5V$	-50	-100	-180	-50	-180	mA
ICCH		V_{CC} = 5.5V; Outputs High, V_{I} = GND or V_{CC}		65	250		250	μΑ
I _{CCL}	Quiescent supply current	V_{CC} = 5.5V; Outputs Low, V_I = GND or V_{CC}		12	15		15	mA
I _{CCZ}		V_{CC} = 5.5V; Outputs 3–State; V _I = GND or V _{CC}		65	250		250	μΑ
		Outputs enabled, one data input at 3.4V, other inputs at V _{CC} or GND; V _{CC} = 5.5V		0.5	1.5		1.5	mA
ΔI_{CC}	Additional supply current per input pin ²	Outputs 3-State, one data input at 3.4V, other inputs at V _{CC} or GND; V _{CC} = 5.5V		50	250		250	μA
		Outputs 3-State, one enable input at 3.4V, other inputs at V_{CC} or GND; $V_{CC} = 5.5V$		0.5	1.5		1.5	mA

NOTES:

1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

2. This is the increase in supply current for each input at 3.4V. 3. This parameter is valid for any V_{CC} between 0V and 2.1V, with a transition time of up to10msec. From V_{CC} = 2.1V to V_{CC} = 5V \pm 10%, a transition time of up to 100µsec is permitted.

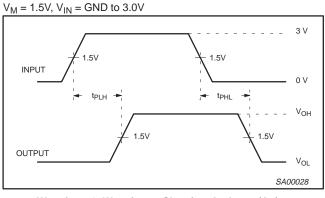
AC CHARACTERISTICS

GND = 0V; t_R = t_F = 2.5ns; C_L = 50pF, R_L = 500 Ω

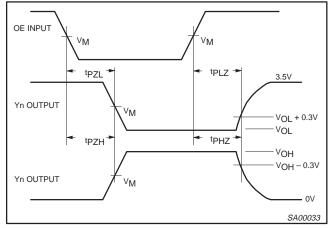
					LIMIT	ſS		
SYMBOL	PARAMETER	WAVEFORM	T _a V	_{amb} = +25° ′cc = +5.0′	C V	$T_{amb} = -40^{\circ}$ $V_{CC} = +5.$	°C to +85°C .0V ±0.5V	UNIT
			Min	Тур	Мах	Min	Max	
t _{PLH} t _{PHL}	Propagation delay An to Yn	1	1.0 1.0	2.9 3.0	4.2 4.3	1.0 1.0	4.4 4.6	ns
t _{PZH} t _{PZL}	Output enable time to High and Low level	2	1.9 1.9	3.2 4.4	5.8 5.9	1.9 1.9	6.5 6.5	ns
t _{PHZ} t _{PLZ}	Output disable time from High and Low level	2	1.0 1.0	4.2 2.9	5.2 4.9	1.0 1.0	5.8 5.5	ns

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AC WAVEFORMS

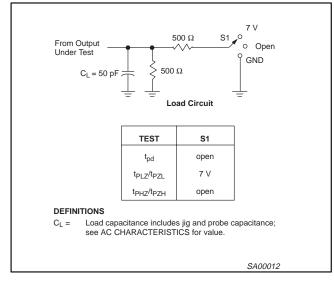


Waveform 1. Waveforms Showing the Input (An) to Output (Yn) Propagation Delays



Waveform 2. Waveforms Showing the 3–State Output Enable and Disable Times

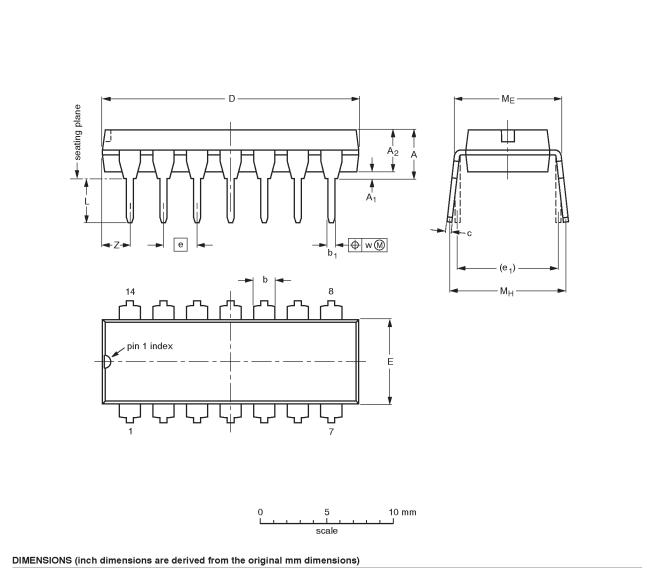
TEST CIRCUIT AND WAVEFORMS



1998 Jan 16

Philips Semiconductors

DIP14: plastic dual in-line package; 14 leads (300 mil)



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	c	D ⁽¹⁾	Е ⁽¹⁾	e	e ₁	L	ME	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

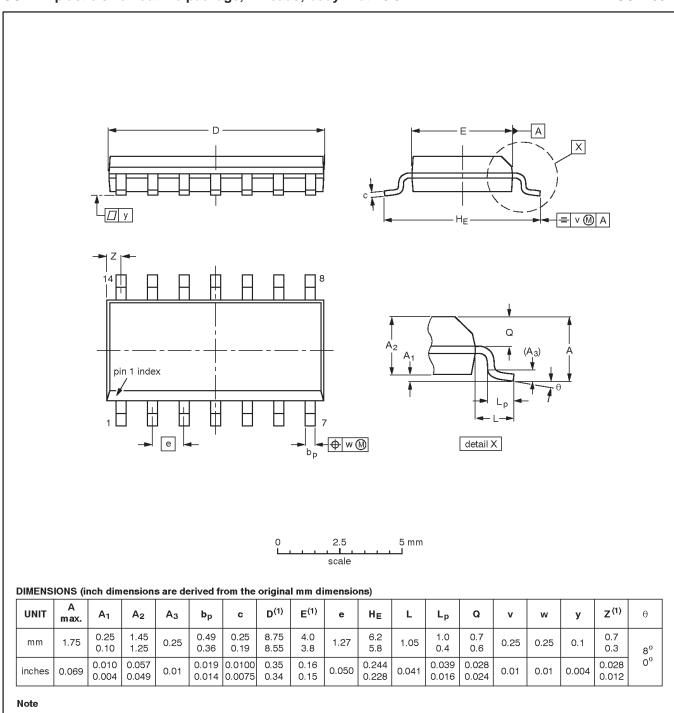
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES				
VERSION	IEC	JEDEC	E EIAJ		PROJECTION	ISSUE DATE	
SOT27-1	050G04	MO-001AA				-92-11-17 95-03-11	

SOT27-1

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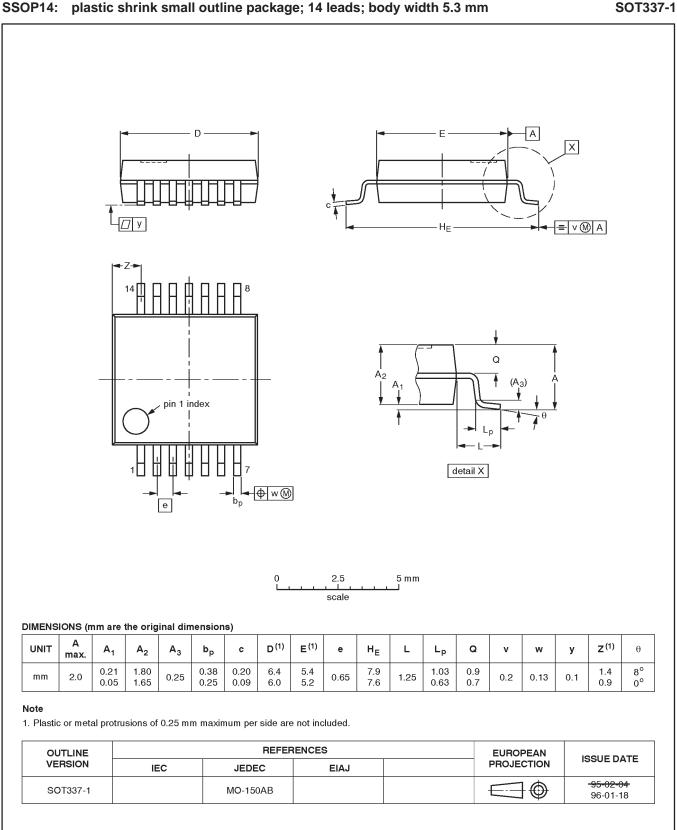
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFEF	RENCES	EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE	
SOT108-1	076E06S	MS-012AB			-95-01-23 97-05-22	

SO14: plastic small outline package; 14 leads; body width 3.9 mm

Product specification

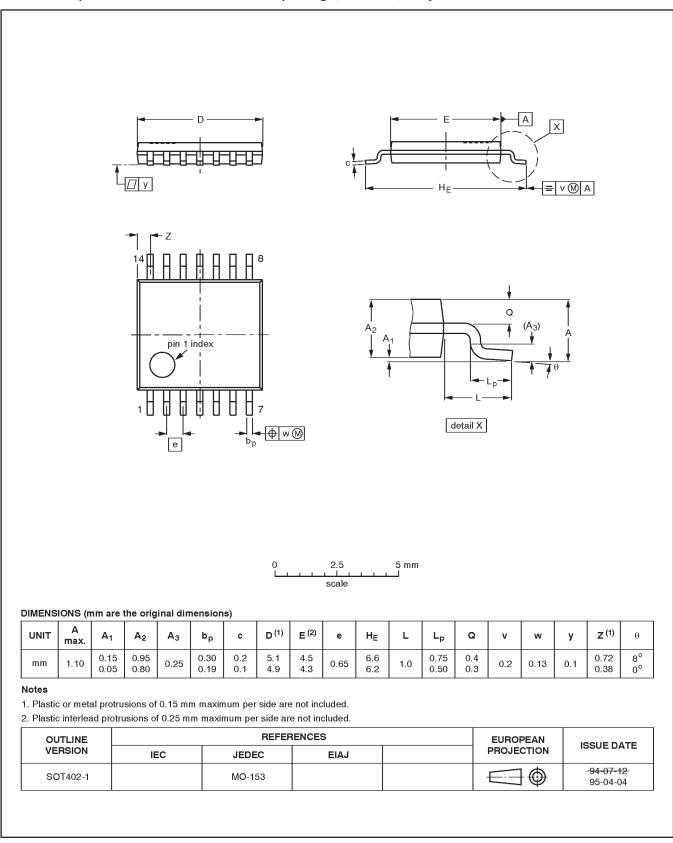
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SOT402-1

74ABT126



TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

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DEFINITIONS						
Data Sheet Identification	Product Status	Definition				
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.				
Preliminary Specification	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.				
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